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What's New

Modelithics Releases the COMPLETE+3D Library v19.6 for ANSYS HFSS with 117 New Full Wave Electromagnetic Models

[Press Release](#)[Release Notes](#)[Library Brochure](#)

Modelithics Releases the Qorvo GaN Library v19.4.2
Includes new model for QPD1006 internally-matched CW-capable discrete GaN

[Press Release](#)[Release Notes](#)[Library Brochure](#)

[Request a FREE Trial today for your selected simulator.](#)

Upcoming Events**GOMACTech 2020**

March 16-19 2020

San Diego, CA

[Click here for more information](#)**WAMICON 2020**

April 15-17 2020

Clearwater Beach, FL

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Modelithics & Würth Elektronik Release 20 New Microwave Global Models for Ferrite Beads, Capacitors, and Inductors

Free 90-Day trials available for all Würth component models!

[Press Release](#) [Library Brochure](#)



The Modelithics COMPLETE Library v19.5 Update 4 for Keysight PathWave ADS

[Press Release](#) [Library Brochure](#)

An Efficient and Accurate High-Frequency Diplexer, Duplexer, Triplexer, and N-Plexer Design Flow

Parent Category: 2019 HFE
By: Jeff Kahler
Introduction

Diplexer, duplexer, triplexer, and N-plexer designs may include electrical and physical design requirements that are not only difficult and cumbersome, but at times may seem to be mutually exclusive. This is especially true at high frequencies, typically above ~100MHz and into the multi GHz range, where substrate and interconnect parasitic effects can significantly degrade performance and must be optimized without overburdening the designer or lengthening development time.

An Efficient and Accurate High-Frequency Diplexer, Duplexer, Triplexer, and N-Plexer Design Flow

Quiescent Drain Voltage Dependence of Pulsed I-V Characteristics of GaN HEMTs: Analysis and Modeling

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Abstract—This paper presents an analysis on the dependence of the pulsed I-V characteristics of GaN HEMTs under varying quiescent drain voltage (V_{DQ}) conditions, and how such dependence affects the device performance. It is shown that the quiescent drain voltage dependence of the pulsed I-V characteristics is not only significant, but also varies with the device geometry and the pulse parameters. The dependence of the pulsed I-V characteristics on the quiescent drain voltage is analyzed using a compact model. The dependence of the pulsed I-V characteristics on the quiescent drain voltage is analyzed using a compact model. The dependence of the pulsed I-V characteristics on the quiescent drain voltage is analyzed using a compact model.

Quiescent Drain Voltage Dependence of Pulsed I-V Characteristics of GaN HEMTs: Analysis and Modeling

Literature & Presentations

Check out our new and updated Literature & Presentations!

- [Modelithics COMPLETE+3D Library for ANSYS HFSS Brochure](#)
- [Modelithics Qorvo GaN Library v19.4.2 Release Notes](#)



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